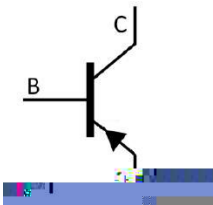


Rev.E Mar.-2016

KF \$0) GE G Silicon PNP transistor in a TO-92 Plastic Package.

High P_C and I_C .

Medium power amplifier applications.

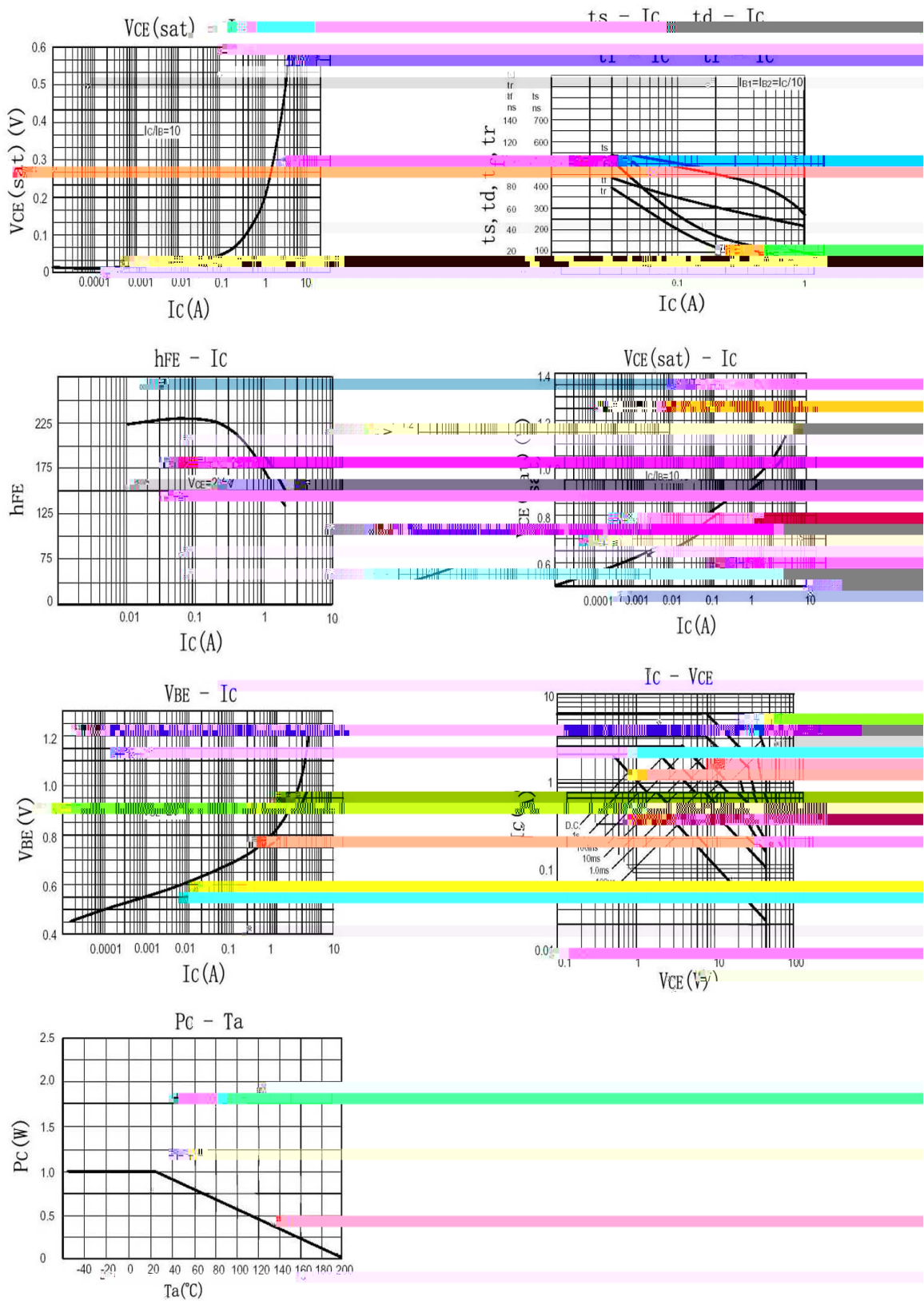


PIN 1 Collector PIN 2 Base PIN 3 Emitter

See Marking Instructions.

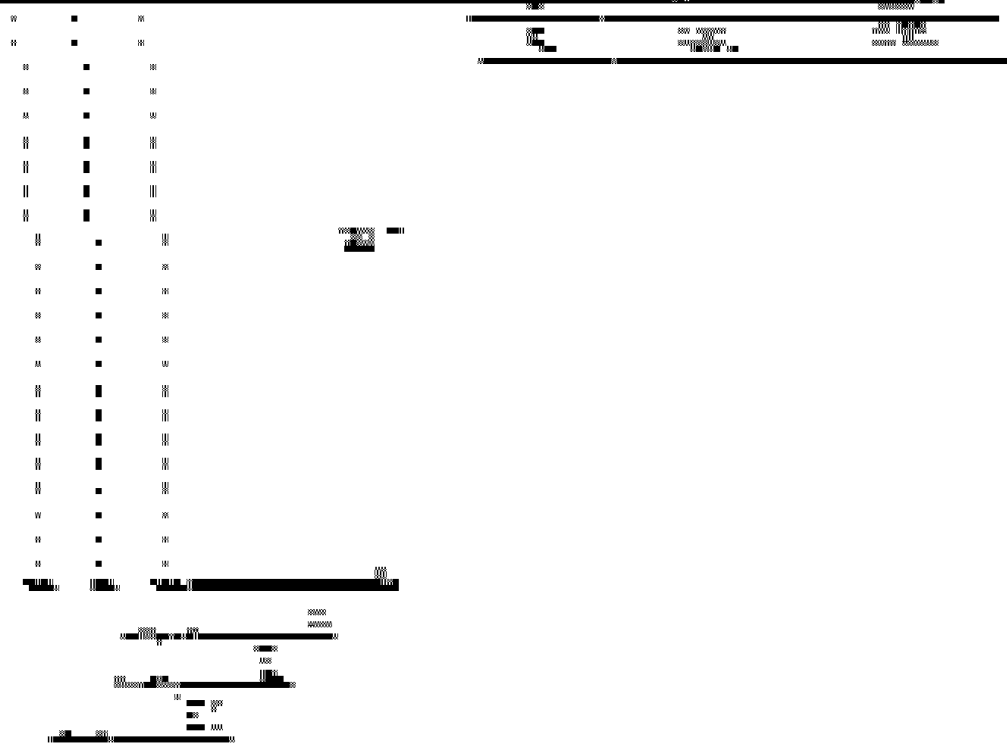
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-2.0	A
Peak Collector Current- Continuous	I_{CM}	-6.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

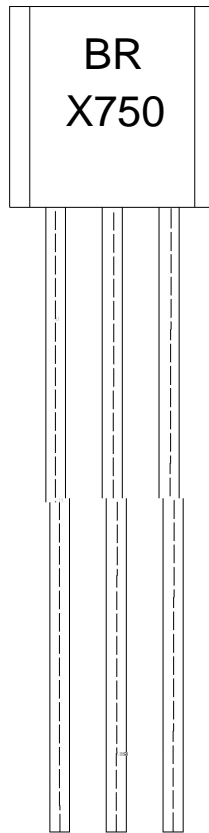
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$	-60			V
Collector to Emitter Breakdown Voltage	V	$I = -10mA$	-45			V



TO-92

Unit: mm





9| 1

0.

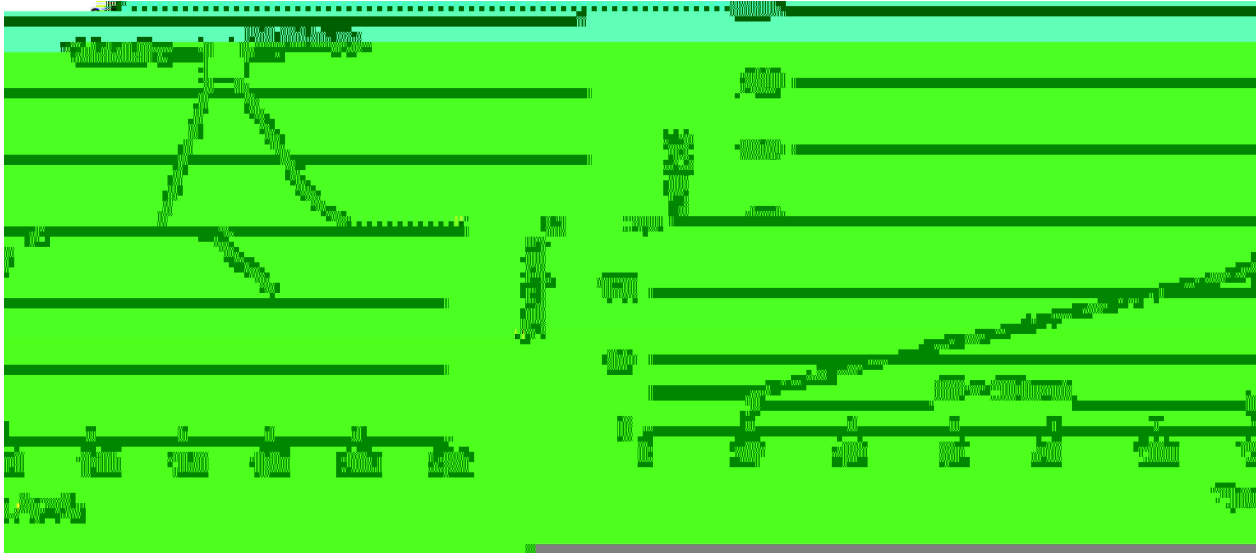
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Note:

BR: Company Code.

X750: Product Type.

****: Lot No. Code,code change with Lot No.



- 1 25 150 60 90sec;
- 2 255..5 5..0.5sec;
- 3 2 10 /sec.

Note:

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255..5 , Duration:5..0.5sec.
- 3. Cooling Speed: 2~10 /sec.

270..5

10..1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type	Units				Dimension		(unit mm ³)

/ AMMO

Package Type	Units	Dimension	(unit mm ³)